

MOS Field Effect Transistor

2SK3365

■ Features

- Super low on-state resistance:
 $R_{DS(on)1} = 14 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 15 \text{ A)}$
 $R_{DS(on)2} = 21 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 15 \text{ A)}$
 $R_{DS(on)3} = 29 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4 \text{ V, } I_D = 15 \text{ A)}$
- Low C_{iss} : $C_{iss} = 1300 \text{ pF TYP.}$
- Built-in gate protection diode

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	±30	A
	I _{dp} *	±120	A
Power dissipation T _A =25℃ T _C =25℃	P _D	1.0	W
		36	
Channel temperature	T _{ch}	150	℃
Storage temperature	T _{stg}	-55 to +150	℃

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$			± 10	μA
Gate cutoff voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	1.5	2.0	2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=15\text{A}$	8.0	16.0		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=15\text{A}$		11.5	14	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=15\text{A}$		15.2	21	$\text{m}\Omega$
		$V_{GS}=4.0\text{V}, I_D=15\text{A}$		18	29	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		1300		pF
Output capacitance	C_{oss}			405		pF
Reverse transfer capacitance	C_{rss}			190		pF
Turn-on delay time	t_{on}	$I_D=15\text{A}, V_{GS(on)}=10\text{V}, R_G=10\Omega, V_{DD}=15\text{V}$		37		ns
Rise time	t_r			500		ns
Turn-off delay time	t_{off}			75		ns
Fall time	t_f			95		ns
Total Gate Charge	Q_G	$V_{DD} = 24\text{V}, V_{GS} = 10 \text{ V, } I_D = 30\text{A}$		25		nC
Gate to Source Charge	Q_{GS}			4.5		nC
Gate to Drain Charge	Q_{GD}			7.0		nC

